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Form PTO-1449 (REV. 8-83)	orm PTO-1449 US Dept. of Commerce			ATTY DOCKET NO. 119232				APPLICATION NO. 10/807,235		
INFORMATION DISCLOSURE STATEMENT										
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E.P.	4.	European Search Report dated September 19, 2005								
ES	5.	Osten, et al., Epitaxial Praseodymium Oxide: A new high-K dielectric, pp. 100-106, JWGI (2001)								
60	6.	Liu, et al., Epitaxial growth of Pr <sub>2</sub> O <sub>3</sub> o	n Si(1	III) and the	observation of a hexagonal t	o cubic phase	transition du	ring		
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	7.	Ferrari, et al., Chlorine mobility during	anne	aling in No	in ZrO <sub>2</sub> and HfO <sub>2</sub> films grow	m by atomic la	ver denogitiv			
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27	8.	Murawala, et al., Plasma Enhanced Liquid Source-CVD and Rapid Thermal Annealing of Tantalum Penta Oxide Dielectric Material, Materials, Tsukuba, pp. 527-529 (1992)								
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